

EAST Search History**EAST Search History (Prior Art)**

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	(@ad<="19950130") and via and "etch stop" and "hard mask" and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:00
S2	11	(@ad<="19950130") and via and "etch stop" and "hard mask" and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:50
S3	2	("5328533").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:05
S4	2	("5328553").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:05
S5	19	(@ad<="19950130") and via and ("etch stop" or etchstop) and ("hard mask" or hardmask) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:51
S6	8	(@ad<="19950130") and via and ("etch stop" or etchstop) and ("hard mask" or hardmask) and conductor not S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:52
S7	21	(@ad<="19950130") and via and ("etch stop" or etchstop) and (fourth with (insulator or dielectric)) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:53

S8	29	(@ad<="19950130") and via and ("etch stop" or etchstop) and (fourth with (insulat\$3 or dielectric)) and conductor	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:53
S9	2	("5328553").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:50
S10	2	("20040175952").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:52
S11	5520	(@ad<="19950130") and (438/69\$.ccls.)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:58
S12	428	(@ad<="19950130") and (438/69\$.ccls.) and via	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:58
S13	32	(@ad<="19950130") and (438/69\$.ccls.) and via and ("etch stop" or etchstop)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:59
S14	2	("5240871").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:13
S15	6673	(@ad<="19950130") and ((nitride with etch\$3) same (oxide with etch\$3))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:41
S16	906	(@ad<="19950130") and ((nitride near2 etch\$3) same (oxide near2 etch\$3))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:42

S17	641	(@ad<="19950130") and ((nitride near2 etch\$3) with (oxide near2 etch\$3))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:42
S18	2	("4385937").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:57
S19	215	(@ad<="19950130") and ((nitride near2 etch\$3) with (oxide near2 etch\$3)) and (memory or storage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 17:20
S20	22	(Doan-Trung.in.) or ("Cathey-David.in")	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:18
S21	402	(@ad<="19950130") and ("438"/\$.ccls.) and via and ("etch stop" or etchstop)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:22
S22	99	(@ad<="19950130") and ("438"/\$.ccls.) and via and ("etch stop" or etchstop) and (memory or storage)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:23
S23	3	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (via or trench)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:20
S24	5	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (etch\$3)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:28

S25	2	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (etch\$3) not S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:29
S26	0	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (damascene)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:32
S27	7	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:33
S28	7	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:33
S29	19	(@ad<="19950130") and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch\$3) and damascene	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:56
S30	126	(@ad<="19950130") and (storage or dram or memory) and alignement	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:18
S31	4	(@ad<="19950130") and (storage or dram or memory) and (alignement with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:19

S32	8855	(@ad<="19950130") and (storage or dram or memory) and (aligned with (hole or via or contact))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:20
S33	689	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:21
S34	274	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and (first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) and (etch\$3)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:24
S35	136	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) and (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:25
S36	69	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) with (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:25
S37	18	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) with (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3) with (third near2 (dielectric or insulat\$4 or isolat\$3)))	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:26

S38	3	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat\$4 or isolat\$3)) with (second near2 (dielectric or insulat\$4 or isolat\$3)) with (etch\$3) with (third near2 (dielectric or insulat\$4 or isolat\$3))) and stop	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:28
S39	32	("4252840" "4758528" "4974040" "5150278" "5196910" "5240871" "5281549" "5292677" "5324681" "5328553" "5338700" "5476806" "5479054" "5502336" "5605857" "6744091").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 13:30
S40	2	("20040175952").PN.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 14:50
S41	1	S40 and (fourth with insulation with side\$1wall with conductor)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 14:50
S42	54	(EMA-T\$).in. and insulation.clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:19
S43	31	(EMA-T\$).in. and insulation.clm. and step.clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:19
S44	24	(EMA-T\$).in. and insulation.clm. and step.clm. and etching.clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:20
S45	8	(EMA-T\$).in. and insulation.clm. and step.clm. and etching.clm. and stopper.clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:20

S46	4	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor near2 memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:38
S47	4	(@ad<="19950130") and (etch\$3 near1 stop) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:45
S48	4	(@ad<="19950130") and (etch\$3 near1 stop\$4) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:46
S49	5	(@ad<="19950130") and (etch\$3 near1 stop\$4) and (hardmask or hard\$1mask) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:47
S50	1	(@ad<="19950130") and (etch\$3 near1 stop\$4) and (hardmask or hard\$1mask) and (transistor with memory) not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:47
S51	1	(@ad<="19950130") and (etch\$3 near2 stop\$4) and (hardmask or hard\$1mask) and (transistor with memory) not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:51
S52	418	(@ad<="19950130") and (etch\$3 near2 stop\$4) and (transistor with memory) not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:58
S53	324	(@ad<="19950130") and (etch\$3 near2 stop\$4) and (transistor with memory) and mask and contact not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:05

S54	307	(@ad<="19950130") and (etch\$3 near2 stop\$4) and (transistor with memory) and mask and contact not S48 and insulat\$3	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:06
S55	62	(@ad<="19950130") and (etch\$3 near2 stop\$4) and (transistor with memory) and mask and contact not S48 and (insulat\$3 with fourth)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:06
S56	27	(@ad<="19950130") and (etch\$3 near2 stop\$4) and (transistor with memory) and mask and contact not S48 and (insulat\$3 with fourth with etch\$3)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:11
S57	3	(anezaki-t\$).in. and insulation.clm. and step.clm. and etching.clm. and stopper.clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:19
S58	194	("257"/\$).ccls. and insulation.clm. and step.clm. and etching.clm. and stopper.clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:20
S59	57	("257"/\$).ccls. and insulation.clm. and step.clm. and etching.clm. and stopper.clm. and (memory with transistor)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:21
S60	63	("257"/\$).ccls. and insulation.clm. and step.clm. and etching.clm. and (etch\$3 near1 stop\$3).clm. and (memory with transistor)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:22
S61	88	("257"/\$).ccls. and insulation.clm. and contact.clm. and etching.clm. and (etch\$3 near1 stop\$3).clm. and (memory with transistor)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:22
S62	349	("257"/\$).ccls. and ((insulat\$3 or dielectric) with first).clm. and contact.clm. and etching.clm. and (etch\$3 near1 stop \$3).clm. and (memory with transistor)	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:24

S63	0	(438/692).ccls. and ((insulat\$3 or dielectric) with (first and second and fourth)).clm. and contact.clm. and etching. clm. and (etch\$3 near1 stop \$3).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:28
S68	1	(438/694).ccls. and ((insulat\$3 or dielectric) with (first and second and fourth)).clm. and contact.clm. and etching. clm. and (etch\$3 near1 stop \$3).clm.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:41
S69	1038	(438/633).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:42
S70	3350	(438/692).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S71	4413	(438/694).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S72	619	(438/397).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S73	391	(438/715).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S74	70	(257/E21.017).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44
S75	1267	(257/E21.575).ccls.	US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44

S76	1445	(216/18).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44
S77	12050	S69 S70 S71 S72 S73 S74 S75 S76	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44
S78	4	(@ad<="19950130") and (etch\$3 near1 stop\$4) and (hardmask or hard\$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 15:45
S79	5	(@ad<="19950130") and S77 and (etch\$3 near2 stop\$4) and (transistor with memory) and mask and contact not S78 and (insulat\$3 with fourth with etch\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 15:45
S80	2	("5384287").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/20 10:32
S81	2	("20060005483").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/20 11:36
S82	2	("20080152931").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/04/20 11:41

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp

S64	3	(438/692).cls. and ((insulat\$3 or dielectric) with first).clm. and contact.clm. and etching.clm. and (etch\$3 near1 stop\$3).clm. and (memory with transistor)	USPAT; UPAD	OR	OFF	2009/11/25 14:25
S65	23	(438/692).cls. and ((insulat\$3 or dielectric) with first).clm. and contact.clm. and etching.clm. and (etch\$3 near1 stop\$3).clm.	USPAT; UPAD	OR	OFF	2009/11/25 14:26
S66	20	(438/692).cls. and ((insulat\$3 or dielectric) with (first and second)).clm. and contact.clm. and etching.clm. and (etch\$3 near1 stop\$3).clm.	USPAT; UPAD	OR	OFF	2009/11/25 14:27
S67	0	(438/692).cls. and ((insulat\$3 or dielectric) with (first and second and fourth)).clm. and contact.clm. and etching.clm. and (etch\$3 near1 stop\$3).clm.	USPAT; UPAD	OR	OFF	2009/11/25 14:27

4/20/2010 1:16:17 PM

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